

2SD2222

Silicon NPN triple diffusion planar type Darlington

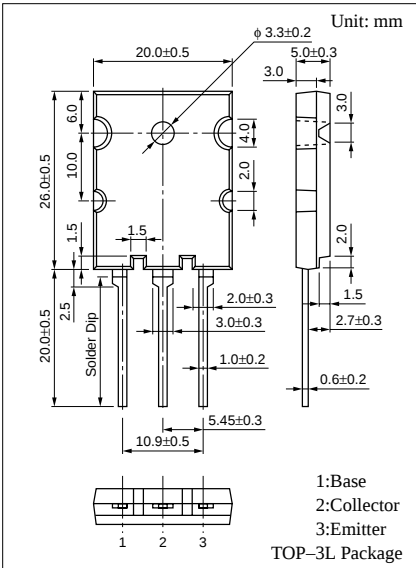
For power amplification
Complementary to 2SB1470

Features

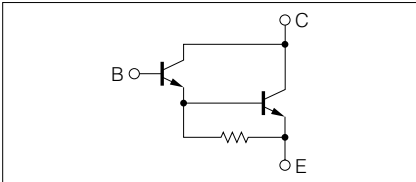
- Optimum for 120W HiFi output
- High forward current transfer ratio h_{FE}
- Low collector to emitter saturation voltage $V_{CE(sat)}$

Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	160	V
Collector to emitter voltage	V_{CEO}	160	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	15	A
Collector current	I_C	8	A
Collector power dissipation	P_C	$T_C=25^{\circ}C$ $T_a=25^{\circ}C$ 150 3.5	W
Junction temperature	T_j	150	$^{\circ}C$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}C$



Internal Connection



Electrical Characteristics ($T_C=25^{\circ}C$)

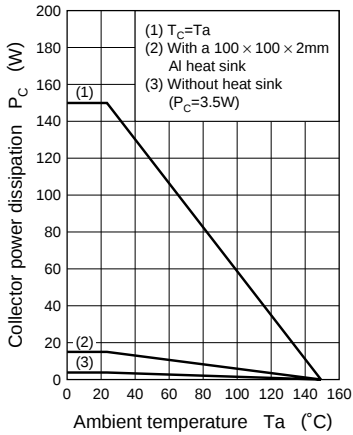
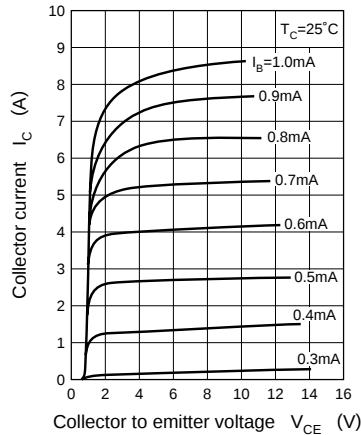
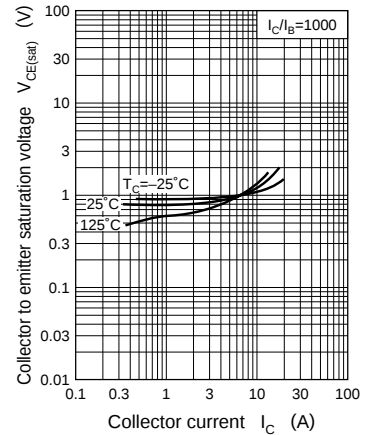
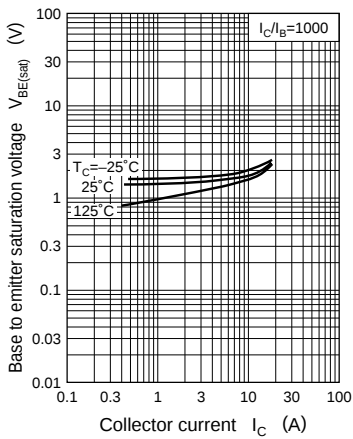
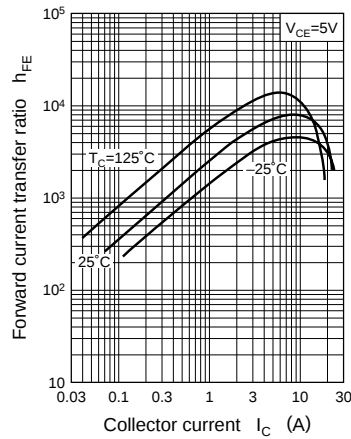
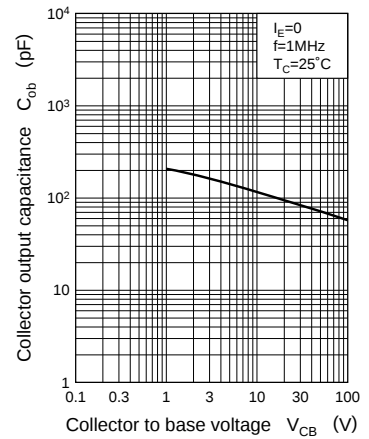
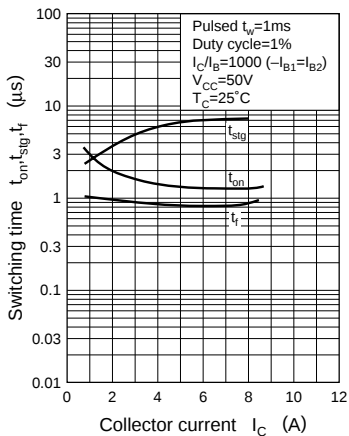
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 160V, I_E = 0$			100	μA
	I_{CEO}	$V_{CE} = 160V, I_B = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			100	μA
Collector to emitter voltage	V_{CEO}	$I_C = 30mA, I_B = 0$	160			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = 5V, I_C = 1A$	10000			
	h_{FE2}^*	$V_{CE} = 5V, I_C = 7A$	3500		20000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 7A, I_B = 7mA$			3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 7A, I_B = 7mA$			3	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 0.5A, f = 1MHz$		20		MHz
Turn-on time	t_{on}	$I_C = 7A, I_{B1} = 7mA, I_{B2} = -7mA, V_{CC} = 50V$		2		μs
Storage time	t_{stg}			6		μs
Fall time	t_f			1.2		μs

* h_{FE2} Rank classification

Rank	Q	P
h_{FE2}	3500 to 10000	7000 to 20000

Power Transistors

2SD2222

 $P_C - T_a$  $I_C - V_{CE}$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $C_{ob} - V_{CB}$  $t_{on}, t_{stg}, t_f - I_C$ 

Area of safe operation (ASO)

